# **Complementary Power Transistors**

## **DPAK for Surface Mount Applications**

Designed for general purpose amplifier and low speed switching applications.

#### **Features**

- Lead Formed for Surface Mount Applications in Plastic Sleeves (No Suffix)
- Straight Lead Version in Plastic Sleeves ("-1" Suffix)
- Electrically Similar to MJE2955 and MJE3055
- High Current Gain-Bandwidth Product
- Epoxy Meets UL 94 V-0 @ 0.125 in
- NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

#### **MAXIMUM RATINGS**

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	V <sub>CEO</sub>	60	Vdc
Collector-Base Voltage	V <sub>CB</sub>	70	Vdc
Emitter-Base Voltage	V <sub>EB</sub>	5	Vdc
Collector Current	I <sub>C</sub>	10	Adc
Base Current	Ι <sub>Β</sub>	6	Adc
Total Power Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	P <sub>D</sub> <sup>†</sup>	20 0.16	W W/°C
Total Power Dissipation (Note 1)  @ T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	1.75 0.014	W W/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
ESD - Human Body Model	HBM	3B	V
ESD – Machine Model	MM	С	V

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

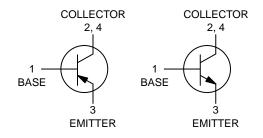


#### ON Semiconductor®

http://onsemi.com

# SILICON POWER TRANSISTORS 10 AMPERES 60 VOLTS, 20 WATTS

#### COMPLEMENTARY





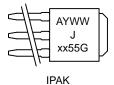


DPAK CASE 369C STYLE 1

IPAK CASE 369D STYLE 1

#### **MARKING DIAGRAMS**





DPAK

A = Assembly Location

Y = Year WW = Work Week Jxx55 = Device Code

x = 29 or 30 G = Pb–Free Package

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

<sup>†</sup>Safe Area Curves are indicated by Figure 1. Both limits are applicable and must be observed.

These ratings are applicable when surface mounted on the minimum pad sizes recommended.

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{ heta JC}$	6.25	°C/W
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{ heta JA}$	71.4	°C/W

<sup>2.</sup> These ratings are applicable when surface mounted on the minimum pad sizes recommended.

# **ELECTRICAL CHARACTERISTICS** ( $T_C = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS			<del>'</del>	+
Collector–Emitter Sustaining Voltage (Note 3) $(I_C = 30 \text{ mAdc}, I_B = 0)$	V <sub>CEO(sus)</sub>	60	-	Vdc
Collector Cutoff Current (V <sub>CE</sub> = 30 Vdc, I <sub>B</sub> = 0)	I <sub>CEO</sub>	-	50	μAdc
Collector Cutoff Current $(V_{CE} = 70 \text{ Vdc}, V_{EB(off)} = 1.5 \text{ Vdc})$ $(V_{CE} = 70 \text{ Vdc}, V_{EB(off)} = 1.5 \text{ Vdc}, T_{C} = 150^{\circ}\text{C})$	I <sub>CEX</sub>	- -	0.02 2	mAdc
Collector Cutoff Current $(V_{CB} = 70 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 70 \text{ Vdc}, I_E = 0, T_C = 150^{\circ}\text{C})$	І <sub>СВО</sub>	- -	0.02 2	mAdc
Emitter Cutoff Current (V <sub>BE</sub> = 5 Vdc, I <sub>C</sub> = 0)	I <sub>EBO</sub>	-	0.5	mAdc
ON CHARACTERISTICS				
DC Current Gain (Note 3) ( $I_C = 4$ Adc, $V_{CE} = 4$ Vdc) ( $I_C = 10$ Adc, $V_{CE} = 4$ Vdc)	h <sub>FE</sub>	20 5	100	-
Collector–Emitter Saturation Voltage (Note 3) $(I_C = 4 \text{ Adc}, I_B = 0.4 \text{ Adc})$ $(I_C = 10 \text{ Adc}, I_B = 3.3 \text{ Adc})$	V <sub>CE(sat)</sub>	- -	1.1 8	Vdc
Base–Emitter On Voltage (Note 3) (I <sub>C</sub> = 4 Adc, V <sub>CE</sub> = 4 Vdc)	V <sub>BE(on)</sub>	-	1.8	Vdc
DYNAMIC CHARACTERISTICS				•
Current–Gain – Bandwidth Product ( $I_C = 500 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f = 500 \text{ kHz}$ )	f⊤	2	-	MHz
(I <sub>C</sub> = 500 mAdc, V <sub>CE</sub> = 10 Vdc, f = 500 kHz)	'	2	_	

<sup>3.</sup> Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2%.

#### **TYPICAL CHARACTERISTICS**

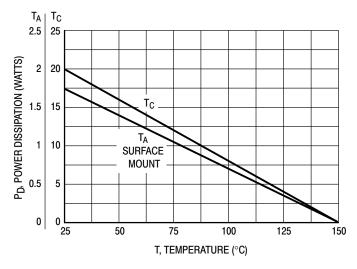


Figure 1. Power Derating

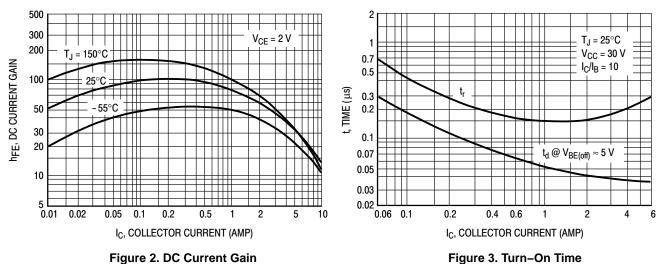


Figure 2. DC Current Gain

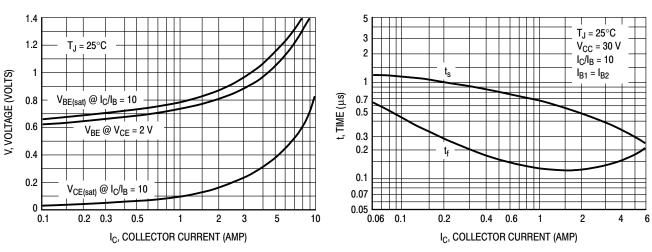


Figure 4. "On" Voltages, MJD3055

Figure 5. Turn-Off Time

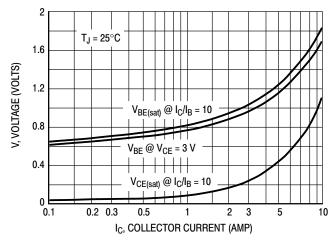
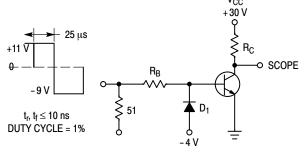


Figure 6. "On" Voltages, MJD2955



 $R_B$  and  $R_C$  VARIED TO OBTAIN DESIRED CURRENT LEVELS  $D_1 \ \text{MUST BE FAST RECOVERY TYPE, eg:} \\ 1N5825 \ \text{USED ABOVE I}_B \approx 100 \ \text{mA} \\ \text{MSD6100 USED BELOW I}_B \approx 100 \ \text{mA} \\ \label{eq:master}$ 

Figure 7. Switching Time Test Circuit

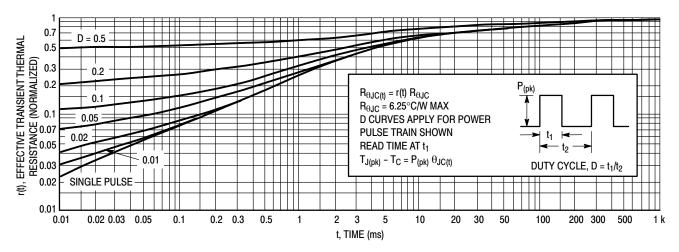


Figure 8. Thermal Response

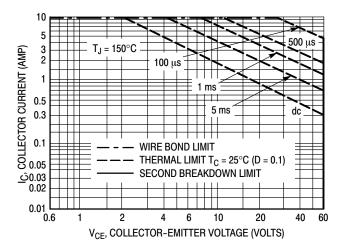


Figure 9. Maximum Forward Bias Safe Operating Area

#### Forward Bias Safe Operating Area Information

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 9 is based on  $T_{J(pk)} = 150^{\circ} C$ ;  $T_{C}$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} \leq 150^{\circ} C$ .  $T_{J(pk)}$  may be calculated from the data in Figure 8. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

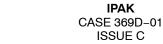
#### **ORDERING INFORMATION**

Device	Package Type	Package	Shipping <sup>†</sup>
MJD2955G	DPAK (Pb-Free)	369C	75 Units / Rail
MJD2955-1G	IPAK (Pb-Free)	369D	75 Units / Rail
MJD2955T4G	DPAK (Pb-Free)	369C	2,500 / Tape & Reel
NJVMJD2955T4G*	DPAK (Pb-Free)	369C	2,500 / Tape & Reel
MJD3055G DPAK (Pb-Free)		369C	75 Units / Rail
MJD3055T4G DPAK (Pb-Free)		369C	2,500 / Tape & Reel
NJVMJD3055T4G*	DPAK (Pb-Free)	369C	2,500 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
\*NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable

# MECHANICAL CASE OUTLINE





STYLE 3: PIN 1. ANODE

2. CATHODE

4. CATHODE

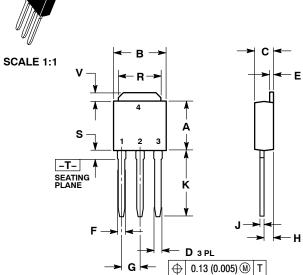
3 ANODE

STYLE 7: PIN 1. GATE 2. COLLECTOR

3. EMITTER

COLLECTOR

**DATE 15 DEC 2010** 



STYLE 2:

PIN 1. GATE

3

STYLE 6: PIN 1. MT1 2. MT2 3. GATE

2. DRAIN

4. DRAIN

MT2

SOURCE

STYLE 1: PIN 1. BASE

3

STYLE 5: PIN 1. GATE

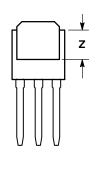
2. ANODE 3. CATHODE

ANODE

2. COLLECTOR

**EMITTER** 

COLLECTOR



#### NOTES:

- DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.235	0.245	5.97	6.35
В	0.250	0.265	6.35	6.73
С	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.090	0.090 BSC		BSC
Н	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.180	0.215	4.45	5.45
S	0.025	0.040	0.63	1.01
٧	0.035	0.050	0.89	1.27
Z	0.155		3.93	

#### MARKING DIAGRAMS

STYLE 4:
PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE
Discrete

XXXXX

ALYWW

XXXXXXXX

X

xxxxxxxxx = Device Code
A = Assembly Location
IL = Wafer Lot
Y = Year
WW = Work Week

	IPAK (DPAK INSERTION MOUNT)		
DOCUMENT NUMBER: 9		Electronic versions are uncontrolled except when accessed directly from Printed versions are uncontrolled except when stamped "CONTROLLED 0"	

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

В

NOTE 7

|  $\oplus$  | 0.005 (0.13) lacktriangledown C

Ħ

Α1

- h3

Ո

**TOP VIEW** 

L3

b2 e

L2 GAUGE

## **DPAK (SINGLE GAUGE)** CASE 369C **ISSUE F** SCALE 1:1 Α

DETAIL A

C SEATING

C-

SIDE VIEW

**DATE 21 JUL 2015** 

#### NOTES:

z

**BOTTOM VIEW** 

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. 2. CONTROLLING DIMENSION: INCHES.
- 3. THERMAL PAD CONTOUR OPTIONAL WITHIN DI-
- MENSIONS b3, L3 and Z.
  4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
  5. DIMENSIONS D AND E ARE DETERMINED AT THE
- OUTERMOST EXTREMES OF THE PLASTIC BODY.

  6. DATUMS A AND B ARE DETERMINED AT DATUM
- 7. OPTIONAL MOLD FEATURE.

	INCHES		MILLIM	ETERS	
DIM	MIN	MAX	MIN	MAX	
Α	0.086	0.094	2.18	2.38	
A1	0.000	0.005	0.00	0.13	
b	0.025	0.035	0.63	0.89	
b2	0.028	0.045	0.72	1.14	
b3	0.180	0.215	4.57	5.46	
С	0.018	0.024	0.46	0.61	
c2	0.018	0.024	0.46	0.61	
D	0.235	0.245	5.97	6.22	
E	0.250	0.265	6.35	6.73	
е	0.090	BSC	2.29 BSC		
Н	0.370	0.410	9.40	10.41	
L	0.055	0.070	1.40	1.78	
L1	0.114	0.114 REF		REF	
L2	0.020	BSC	0.51	BSC	
L3	0.035	0.050	0.89	1.27	
L4		0.040		1.01	
Z	0.155		3.93		

#### ALTERNATE CONSTRUCTIONS **DETAIL A** ROTATED 90° CW **GENERIC** STYLE 1: STYLE 2: STYLE 3: STYLE 4: STYLE 5: PIN 1. CATHODE 2. ANODE 3. GATE 4. ANODE PIN 1. BASE 2. COLLECTOR 3. EMITTER 4. COLLECTOR PIN 1. ANODE 2. CATHODE 3. ANODE 4. CATHODE PIN 1. GATE 2. ANODE 3. CATHODE 4. ANODE PIN 1. GATE 2. DRAIN

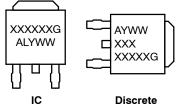
Z

**BOTTOM VIEW** 

С

3. EMITTE 4. COLLE	ER .	3. SOURCE 4. DRAIN	3. ANC 4. CAT	DE	3. GATE 4. ANODE	3.	CATHODE ANODE
STYLE 6: PIN 1. MT1 2. MT2 3. GATE	STYLE 7: PIN 1. GATE 2. COLLE 3. EMITT	ECTOR	E 8: 1. N/C 2. CATHODE 3. ANODE	STYLE 9: PIN 1. ANO 2. CATI 3. RES		2. /	0: CATHODE ANODE CATHODE
4. MT2	4. COLLE		4. CATHODE	4. CATI			ANODE

# **MARKING DIAGRAM\***



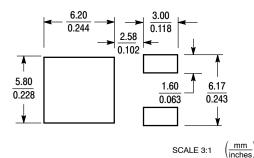
XXXXXX = Device Code = Assembly Location Α L = Wafer Lot Υ = Year WW = Work Week

\*This information is generic. Please refer to device data sheet for actual part marking.

= Pb-Free Package

G

#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DOCUMENT NUMBER:	98AON10527D	Electronic versions are uncontrolled except when accessed directly from the Document Re Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	DPAK (SINGLE GAUGE)		PAGE 1 OF 1

ON Semiconductor and un are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others

ON Semiconductor and the are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at <a href="www.onsemi.com/site/pdf/Patent-Marking.pdf">www.onsemi.com/site/pdf/Patent-Marking.pdf</a>. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor and see no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and

#### **PUBLICATION ORDERING INFORMATION**

LITERATURE FULFILLMENT:
Email Requests to: orderlit@onsemi.com

ON Semiconductor Website: www.onsemi.com

TECHNICAL SUPPORT North American Technical Support: Voice Mail: 1 800-282-9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative